

10V Drive Nch MOSFET

RCX080N25

- **Structure**

Silicon N-channel MOSFET

●Features

- 1) Low on-resistance.
- 2) Low input capacitance.
- 3) High ESD.

● Application

Switching

● Packaging specifications

Type	Package	Bulk
	Code	-
	Basic ordering unit (pieces)	500
RCX080N25		○

● **Absolute maximum ratings** (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	250	V
Gate-source voltage		V_{GSS}	± 30	V
Drain current	Continuous	I_D *3	± 8	A
	Pulsed	I_{DP} *1,3	± 32	A
Source current (Body Diode)	Continuous	I_S	8	A
	Pulsed	I_{SP} *1	32	A
Avalanche current		I_{AS} *2	4	A
Avalanche energy		E_{AS} *2	4.66	mJ
Power dissipation		P_D *4	35	W
Channel temperature		T_{ch}	150	$^{\circ}\text{C}$
Range of storage temperature		T_{stg}	-55 to +150	$^{\circ}\text{C}$

*1 $Pw \leq 10\mu s$, Duty cycle $\leq 1\%$

*2 L=500μH, V_{DD}=50V, R_G=25Ω, T_{ch}=25°C

*3 Limited only by maximum channel temperature allowed.

*4 $T_C=25^{\circ}\text{C}$

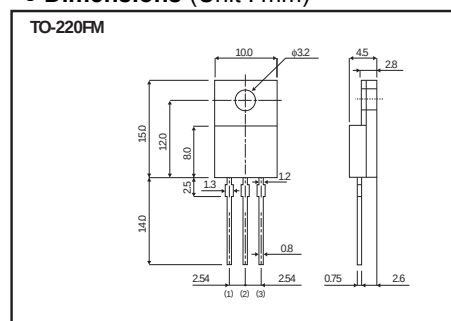
- Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to Case	R _{th} (ch-c)	3.57	°C / W

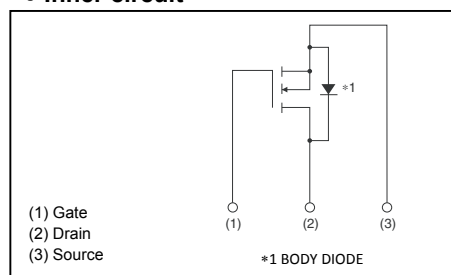
* $T_C=25^{\circ}\text{C}$

* Limited only by maximum channel temperature allowed.

● **Dimensions** (Unit : mm)



- Inner circuit



● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 30V$, $V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	250	-	-	V	$I_D=1mA$, $V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	-	-	10	μA	$V_{DS}=250V$, $V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	3.0	-	5.0	V	$V_{DS}=10V$, $I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	460	600	m Ω	$I_D=4A$, $V_{GS}=10V$
Forward transfer admittance	$ Y_{fs} ^*$	2.2	-	-	S	$V_{DS}=10V$, $I_D=4A$
Input capacitance	C_{iss}	-	840	-	pF	$V_{DS}=25V$
Output capacitance	C_{oss}	-	50	-	pF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	-	25	-	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	22	-	ns	$V_{DD}\approx 125V$, $I_D=4A$
Rise time	t_r^*	-	28	-	ns	$V_{GS}=10V$
Turn-off delay time	$t_{d(off)}^*$	-	28	-	ns	$R_L=31.25\Omega$
Fall time	t_f^*	-	14	-	ns	$R_G=10\Omega$
Total gate charge	Q_g^*	-	15	-	nC	$V_{DD}\approx 125V$, $I_D=8A$
Gate-source charge	Q_{gs}^*	-	6.25	-	nC	$V_{GS}=10V$
Gate-drain charge	Q_{gd}^*	-	5.5	-	nC	$R_L=15.62\Omega$, $R_G=10\Omega$

*Pulsed

● Body diode characteristics (Source-Drain)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD}^*	-	-	1.5	V	$I_s=8A$, $V_{GS}=0V$

*Pulsed

●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics (I)

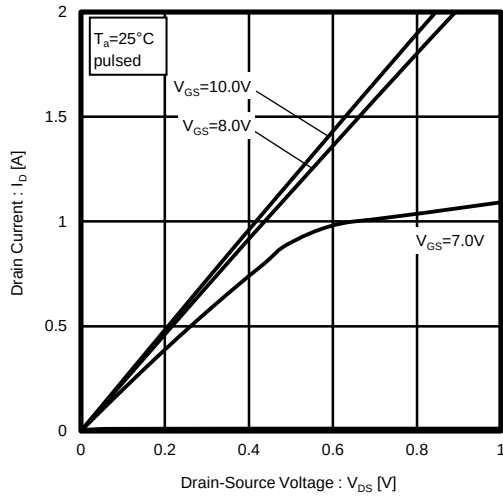


Fig.2 Typical Output Characteristics (II)

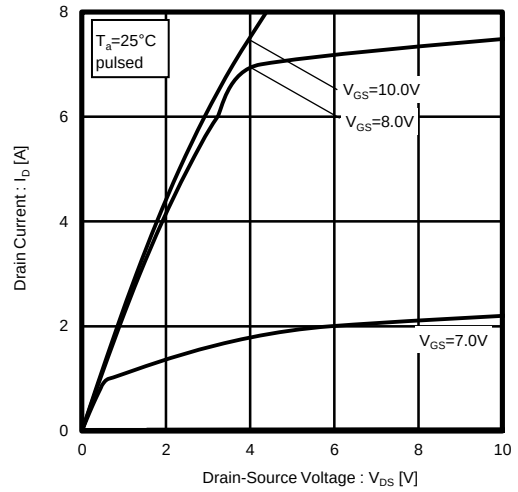


Fig.3 Typical Transfer Characteristics

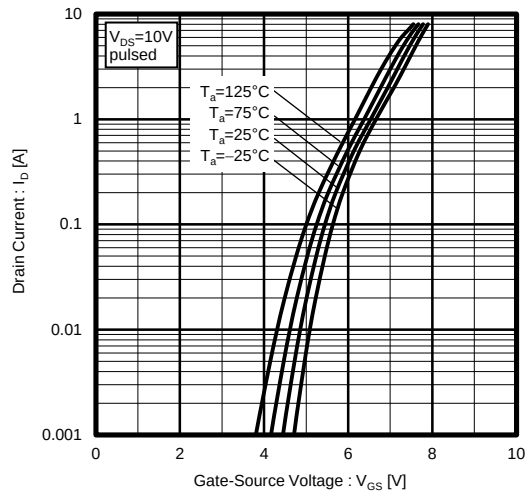


Fig.4 Gate Threshold Voltage vs. Channel Temperature

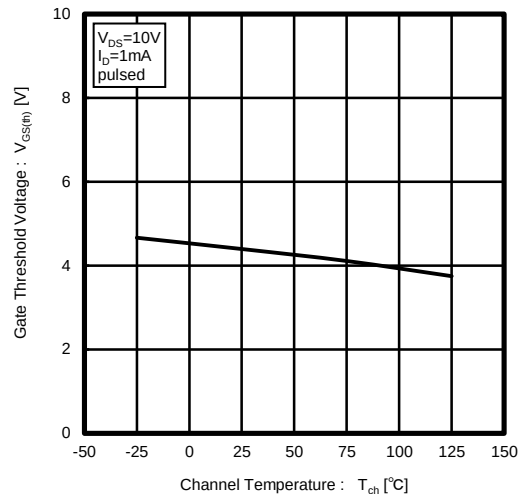


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

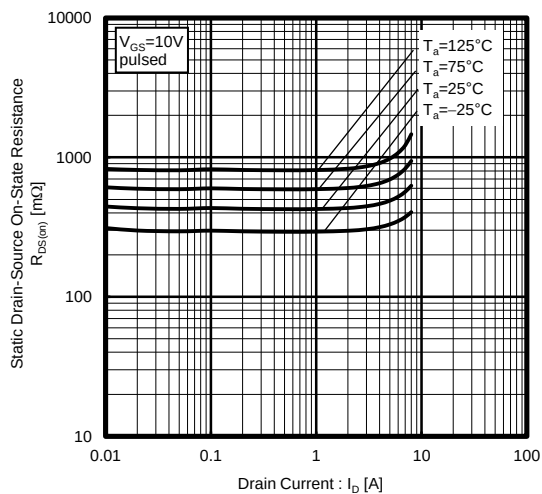


Fig.6 Static Drain-Source On-State Resistance vs. Channel Temperature

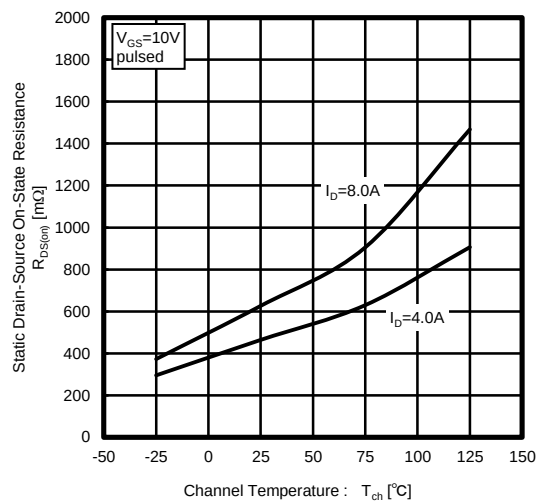


Fig.7 Forward Transfer Admittance vs. Drain Current

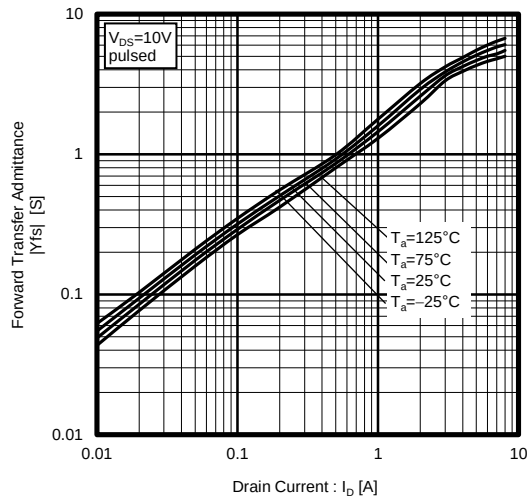


Fig.8 Source Current vs. Source-Drain Voltage

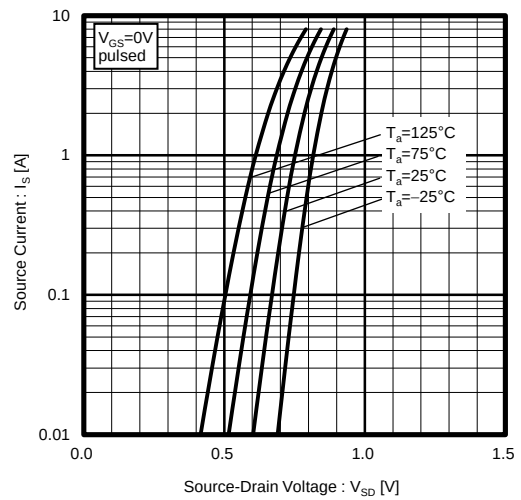


Fig.9 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

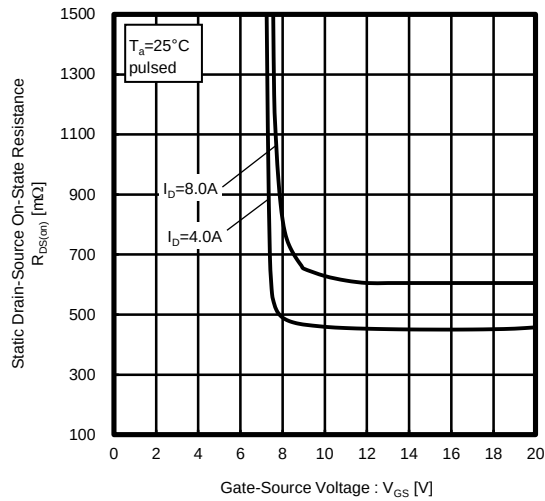


Fig.10 Switching Characteristics

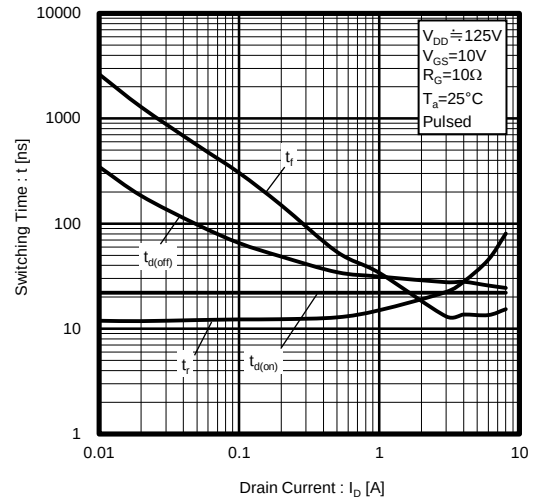


Fig.11 Dynamic Input Characteristics

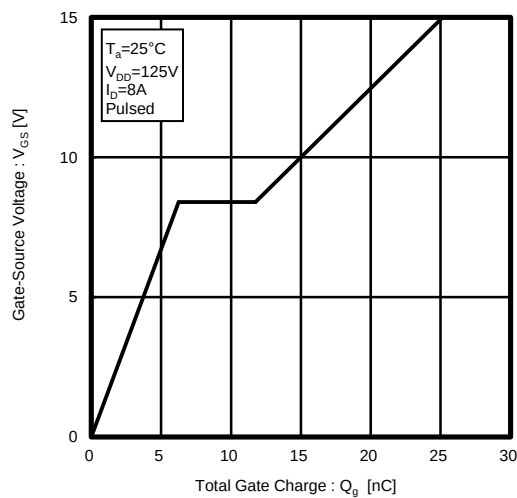


Fig.12 Typical Capacitance vs. Drain-Source Voltage

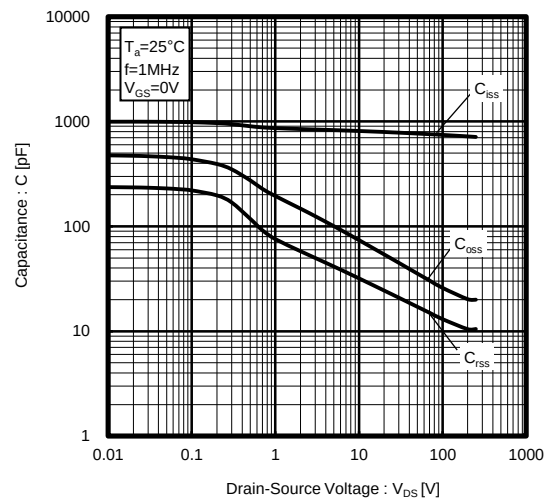
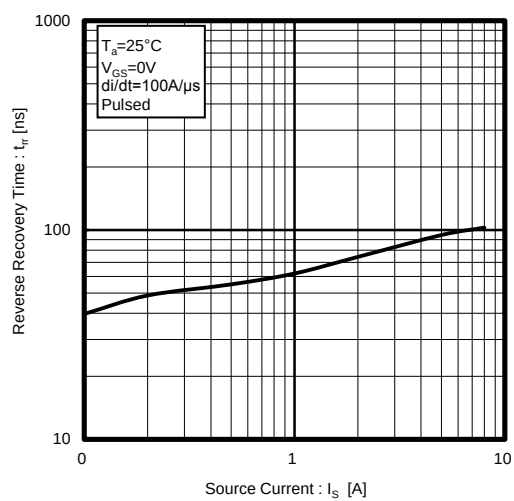


Fig.13 Reverse Recovery Time vs. Source Current



● Measurement circuits

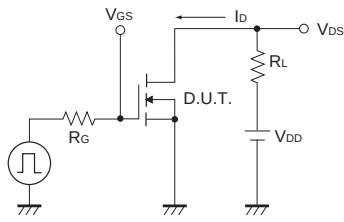


Fig.1-1 Switching Time Measurement Circuit

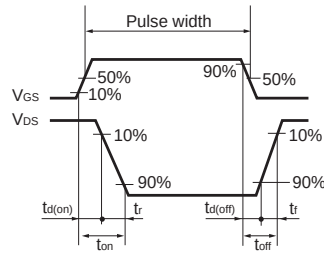


Fig.1-2 Switching Waveforms

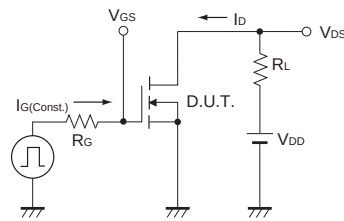


Fig.2-1 Gate Charge Measurement Circuit

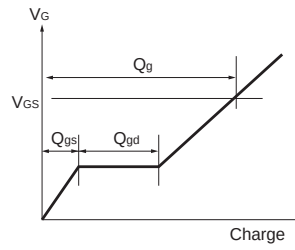


Fig.2-2 Gate Charge Waveform

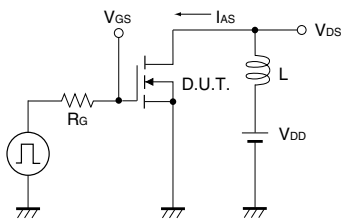


Fig.3-1 Avalanche Measurement Circuit

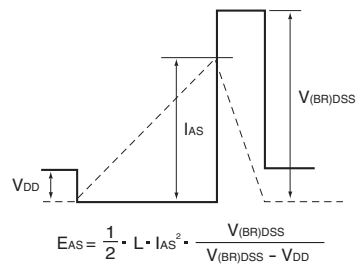


Fig.3-2 Avalanche Waveform

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